



NPN EPITAXIAL SILICON TRANSISTORS

WMBTA92

High Voltage Transistor		SOT—23				
<ul style="list-style-type: none"> * Die Size 0.6X0.6mm * Power Dissipation: 225mW * Collector Current : Max 500mA * Bonding Pad Size Emittoe 100*100mkm base 100*100mkm 				1. BASE 2. EMITTER 3. COLLECTOR		
GUARANTEED PROBED CHARACTERISTICS (TA=25°C)						
Characteristic	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$	300	-	-	V
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=100uA$	300	-	-	V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10uA$	5.0	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=260V$	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V$	-	-	100	nA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=1mA$ $V_{CE}=10V, I_C=10mA$ $V_{CE}=10V, I_C=30mA$	30 40 40	-	-	
Base-Emitter Saturation Voltage	V_{BEsat}	$I_C=20mA, I_B=2mA$	-	-	0.90	V
Collector-Emitter Saturation Voltage	V_{CEsat}	$I_C=20mA, I_B=2mA$	-	-	0.35	V
Transition Frequency	f_r	$V_{CE}=20V, I_C=10mA, f=10MHz$	50	-	-	MHz
Collector-Base Capacitance	C_{cb}	$V_{CB}=20V, f=1MHz$	-	-	6.0	pF
NOTES: Due to probe testing limitations, only the DC parameters are tested.						